

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 30	0.018 at V _{GS} = - 10 V	- 16 ^d	22 nC
	0.0305 at V _{GS} = - 4.5 V	- 16 ^d	

FEATURES

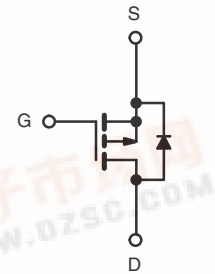
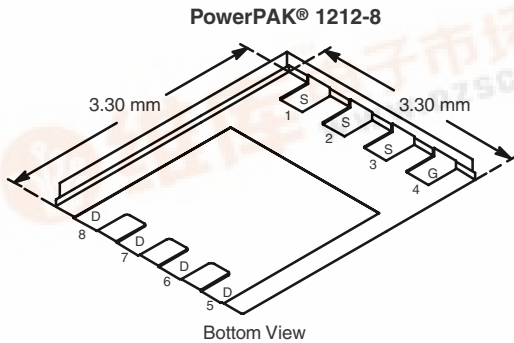
- Halogen-free
- TrenchFET[®] Power MOSFET
- 100% R_g Tested
- 100% UIS Tested



RoHS COMPLIANT

APPLICATIONS

- Notebook Battery Charging
- Notebook Adapter Switch



Ordering Information: Si7121DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 30	V	
Gate-Source Voltage	V _{GS}	± 25		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 16 ^d	
		T _C = 70 °C	- 16 ^d	
		T _A = 25 °C	- 10.6 ^{a, b}	
		T _A = 70 °C	- 8.6 ^{a, b}	
Pulsed Drain Current	I _{DM}	- 50	A	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		- 16 ^d
		T _A = 25 °C		- 3.0 ^{a, b}
Avalanche Current	I _{AS}	- 20	mJ	
Single-Pulse Avalanche Energy	E _{AS}	20		
Maximum Power Dissipation	P _D	T _C = 25 °C	52	
		T _C = 70 °C	33	
		T _A = 25 °C	3.7 ^{a, b}	
		T _A = 70 °C	2.4 ^{a, b}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{e, f}		260		

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	26	33	°C/W
Maximum Junction-to-Case	R _{thJC}	1.9	2.4	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 81 °C/W.
- Package limited.
- See Solder Profile (<http://www.vishay.com/doc?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



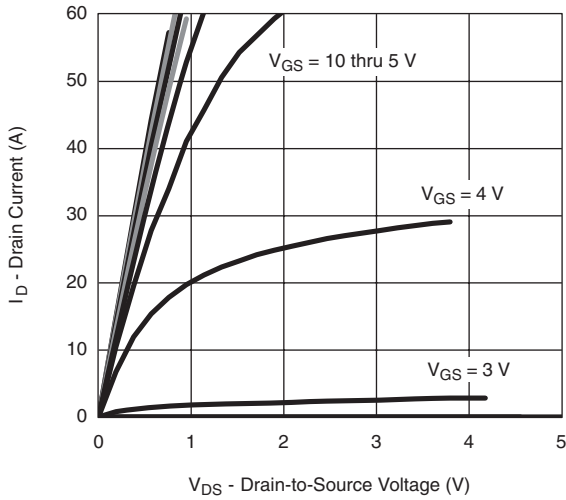
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\ \mu\text{A}$		-31		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		5.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1.0		-3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		0.015	0.018	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$		0.0255	0.0305	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -10\text{ A}$		23		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1960		pF
Output Capacitance	C_{oss}		380			
Reverse Transfer Capacitance	C_{rss}		325			
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		43	65	nC
				22	33	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		6		
Gate-Drain Charge	Q_{gd}			11		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.3	1.3	2.5	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3\ \Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$		11	22	ns
Rise Time	t_r		13	25		
Turn-Off Delay Time	$t_{d(off)}$		32	50		
Fall Time	t_f		9	18		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3\ \Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\ \Omega$		44	70	
Rise Time	t_r		100	160		
Turn-Off Delay Time	$t_{d(off)}$		28	50		
Fall Time	t_f		15	30		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			-16	A
Pulse Diode Forward Current	I_{SM}				-50	
Body Diode Voltage	V_{SD}	$I_S = -2\text{ A}, V_{GS} = 0\text{ V}$		-0.75	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		28	45	ns
Body Diode Reverse Recovery Charge	Q_{rr}		20	40	nC	
Reverse Recovery Fall Time	t_a		13		ns	
Reverse Recovery Rise Time	t_b		15			

Notes:

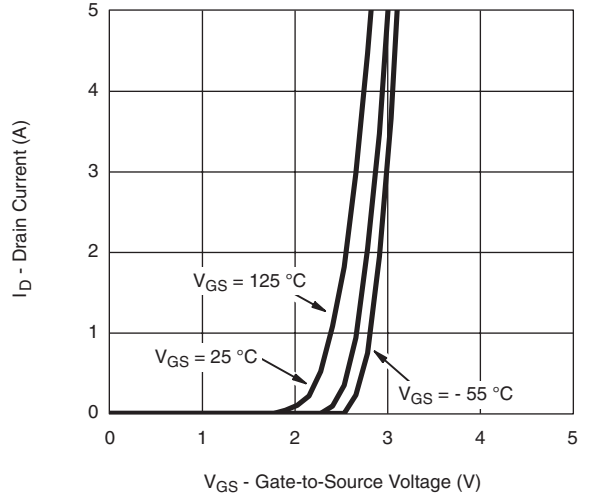
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

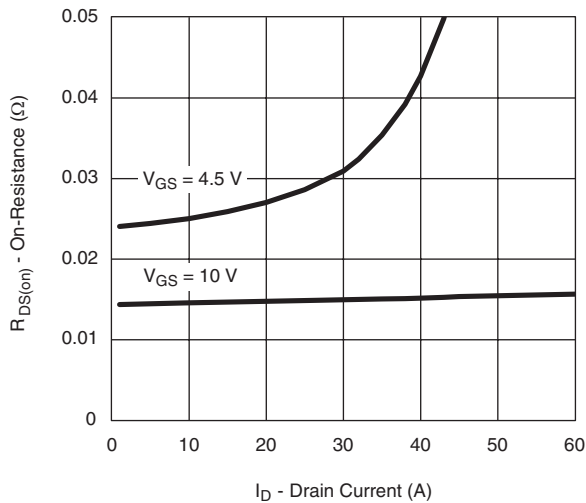
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



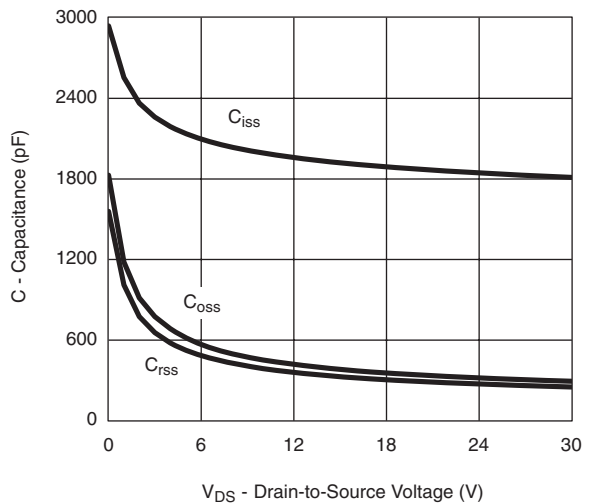
Output Characteristics



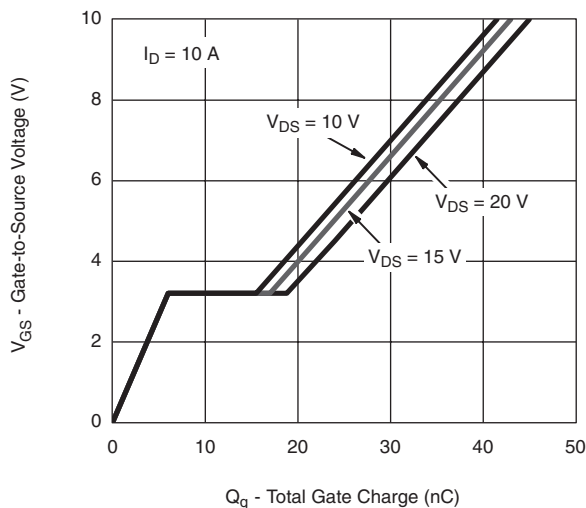
Transfer Characteristics



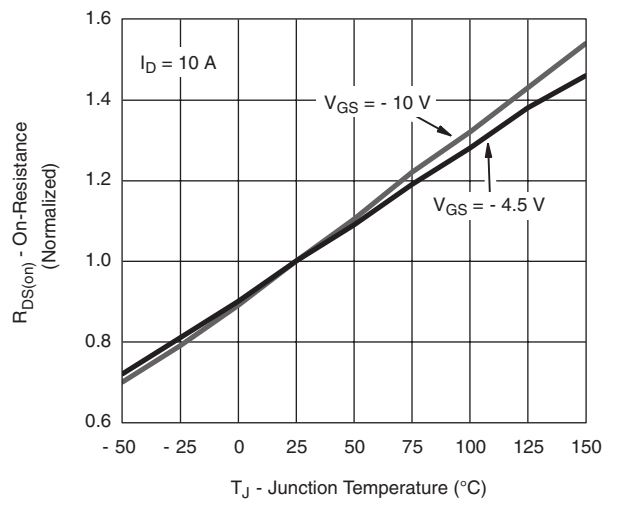
On-Resistance vs. Drain Current



Capacitance



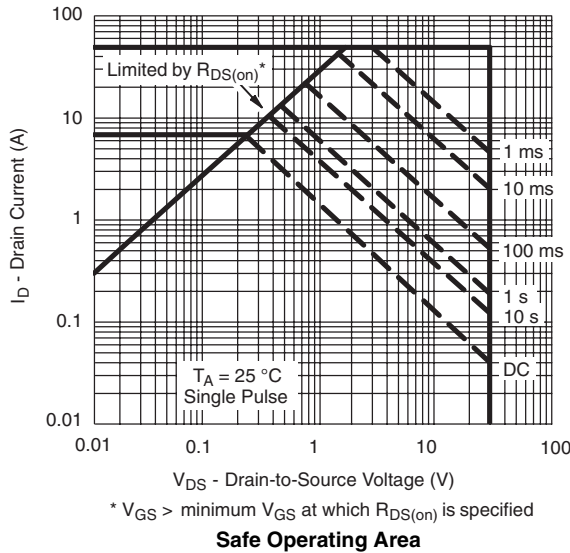
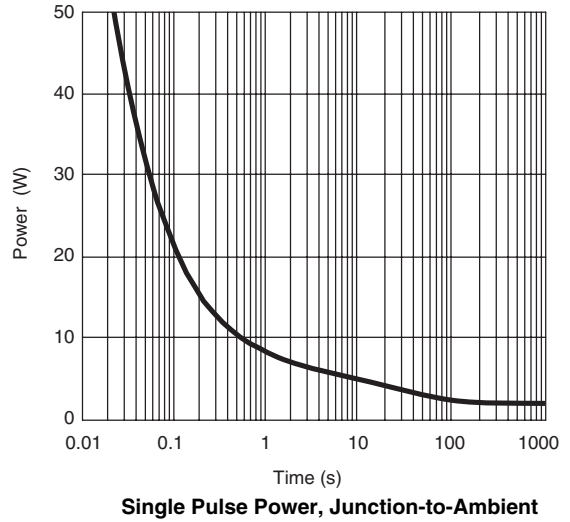
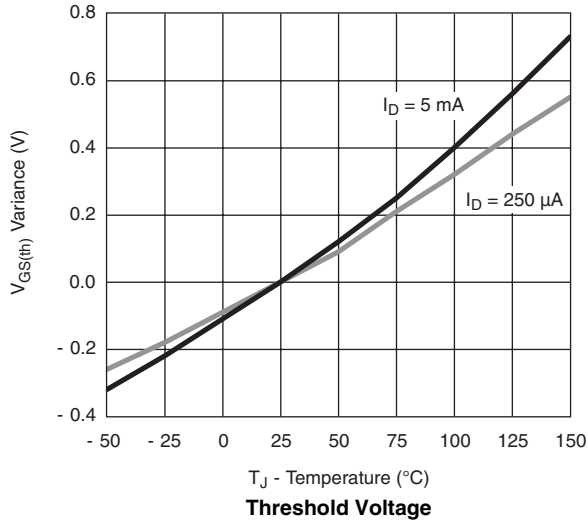
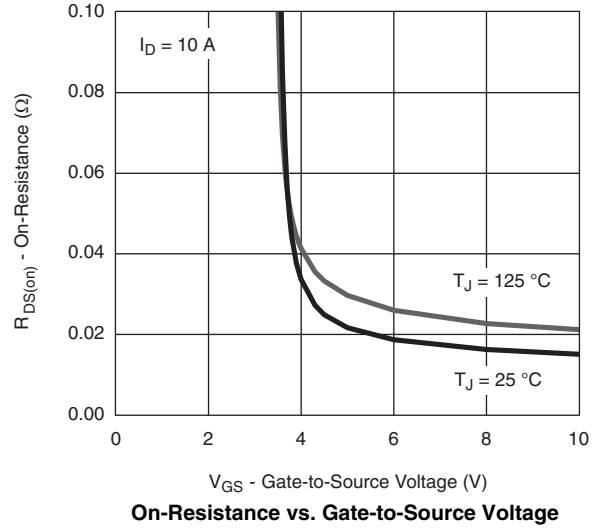
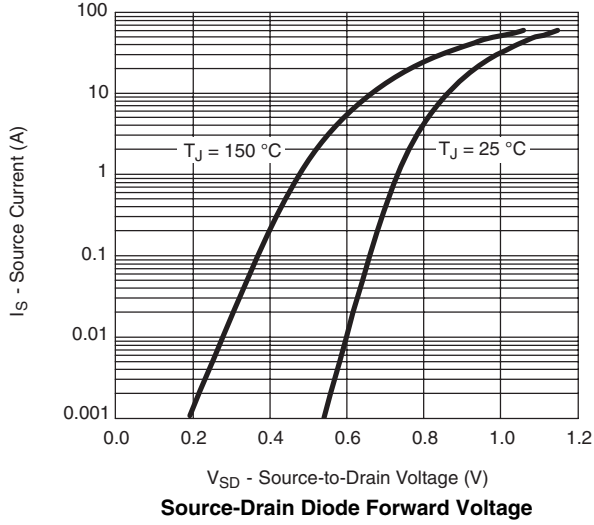
Gate Charge



On-Resistance vs. Junction Temperature

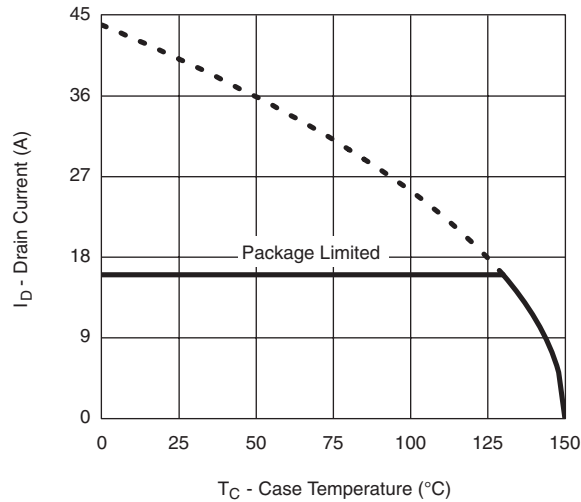


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

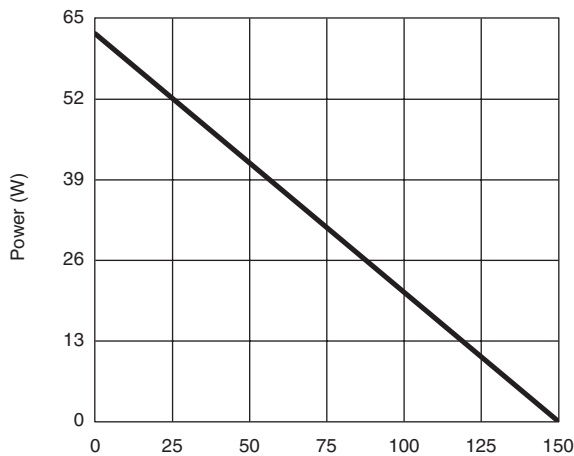




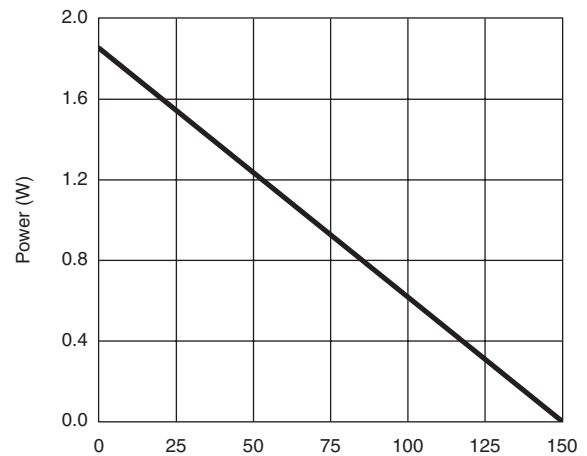
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



Power, Junction-to-Case



Power Derating, Junction-to-Ambient

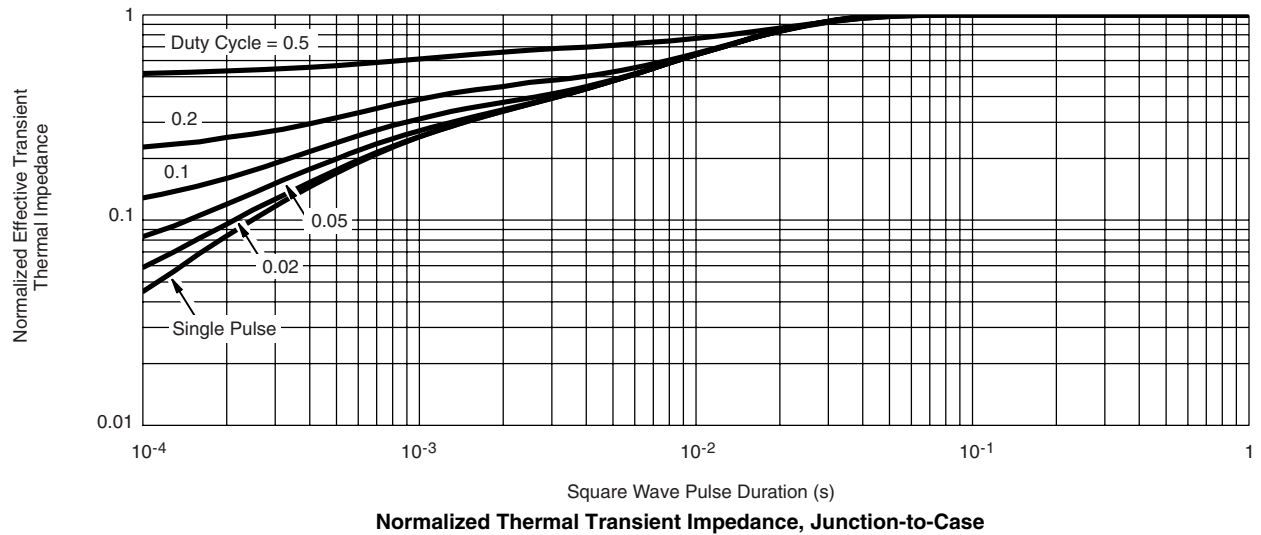
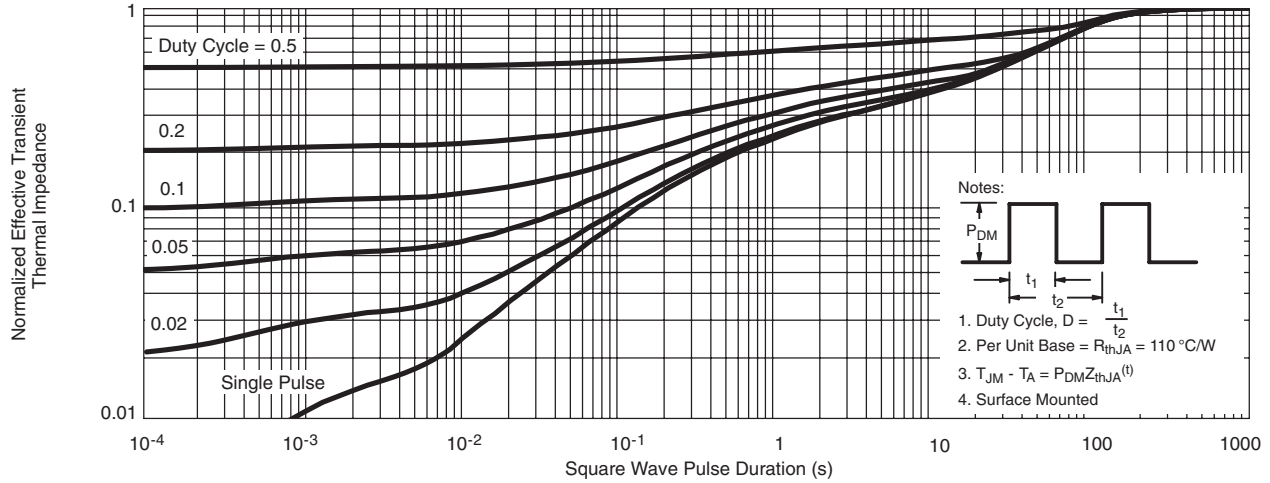
* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si7121DN



Vishay Siliconix 供应商

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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